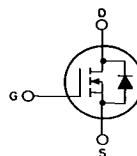


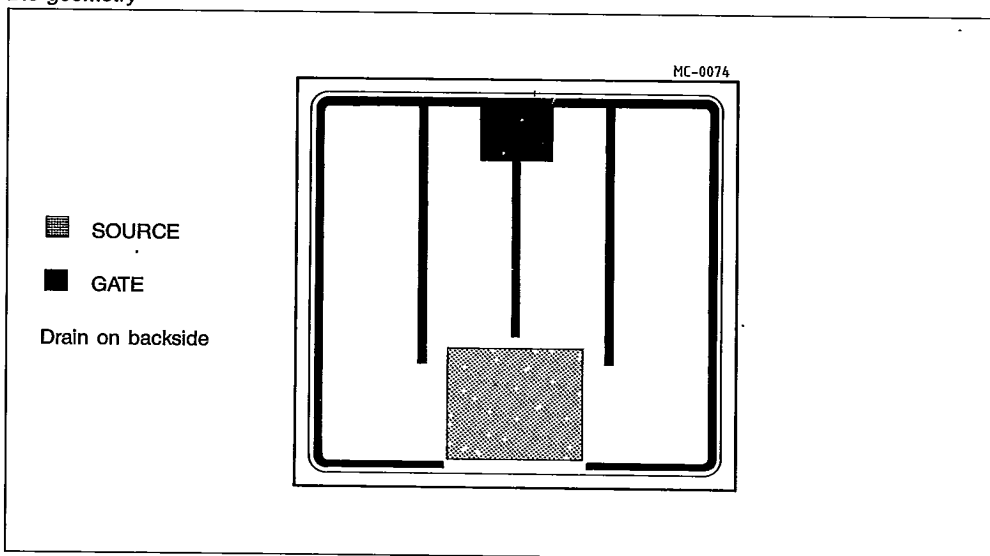
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR IN DIE FORM

- **DIE SIZE:** 156 × 156 mils
- **METALLIZATION:**
 - Top Al
 - Back Au/Cr/Ni/Au
- **BACKSIDE THICKNESS:** 6100 Å
- **DIE THICKNESS:** 16 ± 2 mils
- **PASSIVATION:** P-Vapox
- **BONDING PAD SIZE:**
 - Source 40 × 34 mils
 - Gate 15 × 19 mils
- **RECOMMENDED WIRE BONDING:**
 - Source Al - max 10 mils
 - Gate Al - max 7 mils

SCHEMATIC DIAGRAM

V_{DSS}	$R_{DS(on)}$	I_D^*
200 V	0.4 Ω	9.5 A

N-channel enhancement mode POWER MOS field effect transistor. Easy drive and very fast switching times make this POWER MOS ideal for high speed switching applications.

Die geometry

* With R_{thjc} max. 1.67°C/W

S G S-THOMSON

GUARANTEED PROBED ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$, Note 1)

Parameters		Test Conditions		Min.	Typ.	Max.	Unit
$V_{(BR) DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}$	$V_{GS} = 0$	200			V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_j = 125^\circ\text{C}$				250 1000	μA μA
I_{GSS}	Gate-body leakage current	$V_{GS} = \pm 20 \text{ V}$				100	nA
$V_{GS (th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$	$I_D = 1 \text{ mA}$	2.1		4	V
$R_{DS (on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$	$I_D = 1 \text{ A}$			0.4	Ω

NOTES: 1 - Due to probe testing limitations dc parameters only are tested. They are measured using pulse techniques; pulse width $< 300 \mu\text{s}$, duty cycle $< 2\%$

2 - For detailed device characteristics please refer to the discrete device datasheet